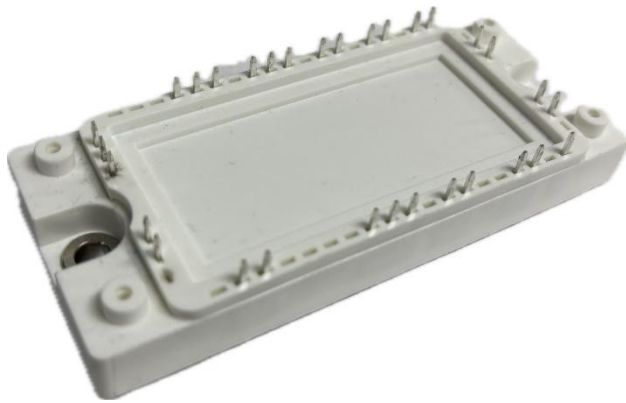




Rectifier/ Brake-chopper Modules

V_{CES} 1600V
 I_F 200A

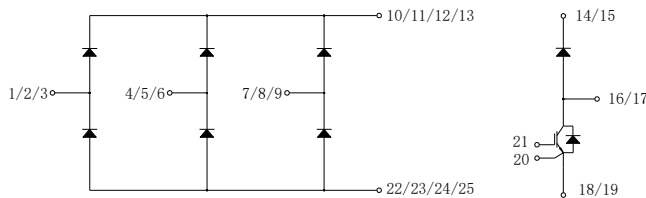
Applications

- Input bridge rectifier
- AC and DC motor control
- Power supply

Features

- Low forward voltage drop
- Small temperature coefficient
- High surge capacity
- Low inductance
- Isolated copper baseplate using DBC technology

Circuit



● Diode- rectifier Characteristics

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}\text{C}$	200	A
Surge Forward Current	I_{FSM}	$V_R=0V, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	1850	A
I^2t -value	I^2t	$V_R=0V, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	17112	A^2s

**Characteristic Values**

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=200A, T_{vj}=25^{\circ}C$		1.13		V
		$I_F=200A, T_{vj}=150^{\circ}C$		1.10		
Reverse Current	I_R	$T_{vj}=150^{\circ}C, V_R=1600V$			2	mA

● IGBT-brake-chopper**Absolute Maximum Ratings**

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	100	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	200	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	442	W



MG200RB16E1A

COMPLIANT
RoHS

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.7mA, T_{vj}=25^{\circ}C$	5.2	5.9	6.4	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.50		V
		$I_C=100A, V_{GE}=15V, T_{vj}=150^{\circ}C$		1.66		
Gate Charge	Q_G			1.01		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		12.7		nF
Reverse Transfer Capacitance	C_{res}			0.065		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=100A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.6\Omega$ $T_{vj}=25^{\circ}C$		195		ns
Rise Time	t_r			31		ns
Turn-off Delay Time	$t_{d(off)}$			306		ns
Fall Time	t_f			201		ns
Energy Dissipation During Turn-on Time	E_{on}			5.96		mJ
Energy Dissipation During Turn-off Time	E_{off}			8.09		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=100A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=3.6\Omega$ $T_{vj}=150^{\circ}C$		205		ns
Rise Time	t_r			36		ns
Turn-off Delay Time	$t_{d(off)}$			384		ns
Fall Time	t_f			339		ns
Energy Dissipation During Turn-on Time	E_{on}			10.4		mJ
Energy Dissipation During Turn-off Time	E_{off}			11.7		mJ
SC Data	I_{sc}	$t_p \leq 8\mu s, V_{GE}=15V, T_{vj}=150^{\circ}C,$ $V_{CC}=600V, V_{CEM} \leq 1200V$		450		A



● Diode-Brake-Chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		15	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	30	A

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=15\text{A}, T_{vj}=25^{\circ}\text{C}$		2.5	2.6	V
		$I_F=15\text{A}, T_{vj}=150^{\circ}\text{C}$		2.4		
Recovered Charge	Q_{rr}	$I_F=15\text{A}$ $V_R=600\text{V}$ $-di_F/dt = 1700\text{A/us}$ $T_{vj}=25^{\circ}\text{C}$		1.25		μC
Peak Reverse Recovery Current	I_{rr}			13		A
Reverse Recovery Energy	E_{rec}			0.44		mJ
Recovered Charge	Q_{rr}	$I_F=15\text{A}$ $V_R=600\text{V}$ $-di_F/dt = 1700\text{A/us}$ $T_{vj}=150^{\circ}\text{C}$		2.58		μC
Peak Reverse Recovery Current	I_{rr}			21		A
Reverse Recovery Energy	E_{rec}			0.98		mJ



● Diode -Chopper-Reverse

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		50	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	100	A

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=50\text{A}, T_{vj}=25^{\circ}\text{C}$		1.98	2.6	V
		$I_F=50\text{A}, T_{vj}=150^{\circ}\text{C}$		1.73		
Recovered Charge	Q_{rr}	$I_F=50\text{A}$		2.19		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 1000\text{A}/\mu\text{s}$		17		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		0.8		mJ
Recovered Charge	Q_{rr}	$I_F=50\text{A}$		6.31		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt = 1000\text{A}/\mu\text{s}$		27		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}\text{C}$		2.34		mJ



● **Module Characteristics** $T_C=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation Voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	4000			V
Maximum Junction Temperature	T_{jmax}				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Thermal Resistance Junction to Case	$R_{\theta\text{JC}}$	per Diode-rectifier			0.364	K/W
		per Diode-brake -chopper			2.14	
		per IGBT-brake-chopper			0.339	
		per Diode-chopper-reverse			0.8	
Thermal Resistance Case to Sink	$R_{\theta\text{CS}}$	per Module		0.009		K/W
Module-to-Sink Torque	M_s		3.0		6.0	N·m
Weight of Module	G			180		g

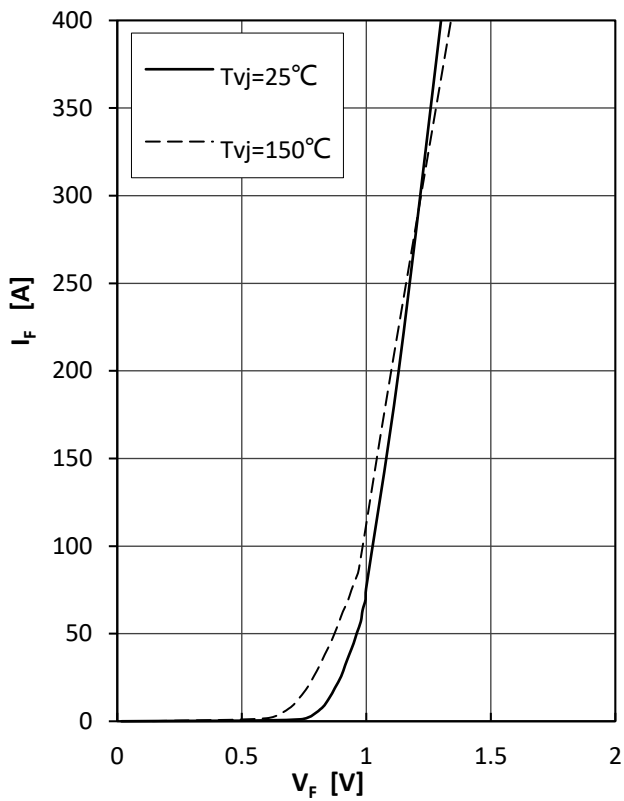


Fig1.Diode-Rectifier
Foward Characteristics

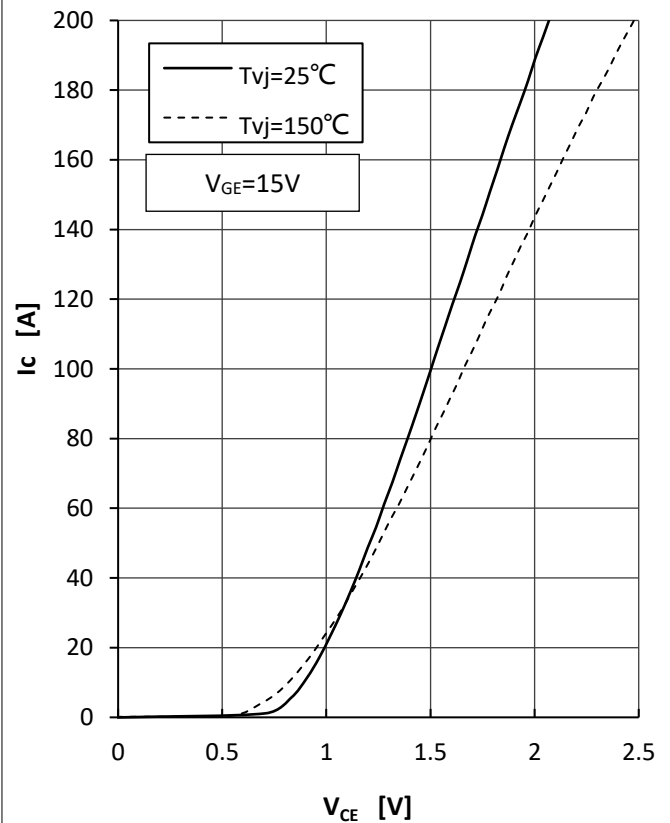


Fig2.IGBT-brake-chopper Output Characteristics

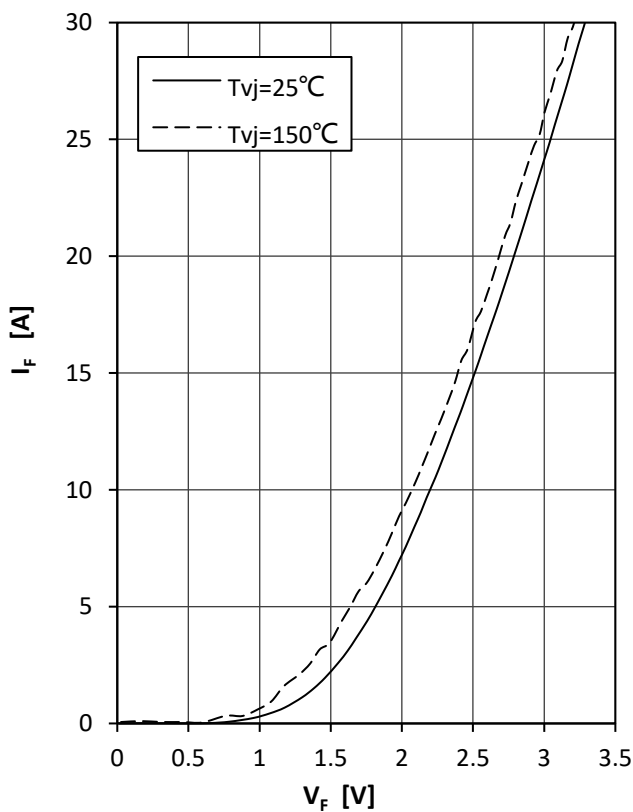


Fig3.Diode-Brake-Chopper
Foward Characteristics

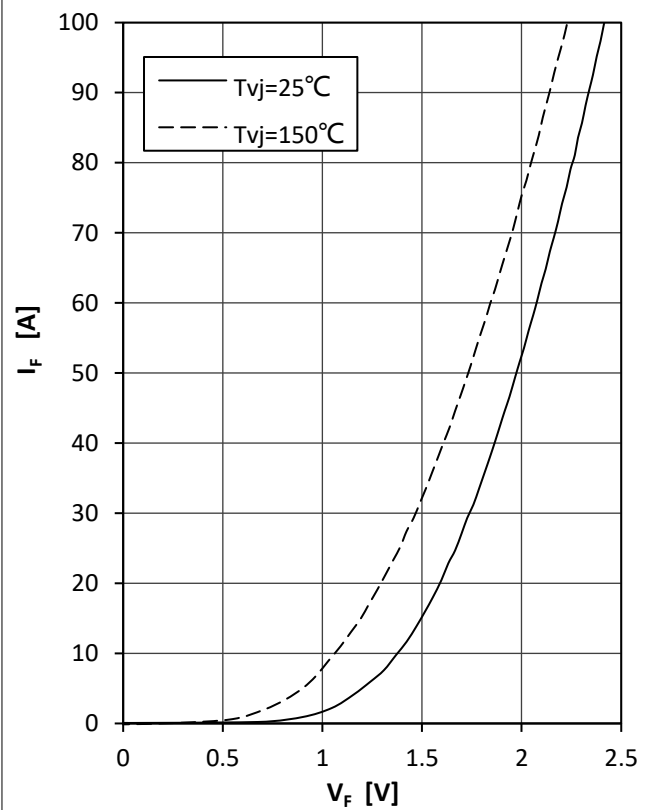
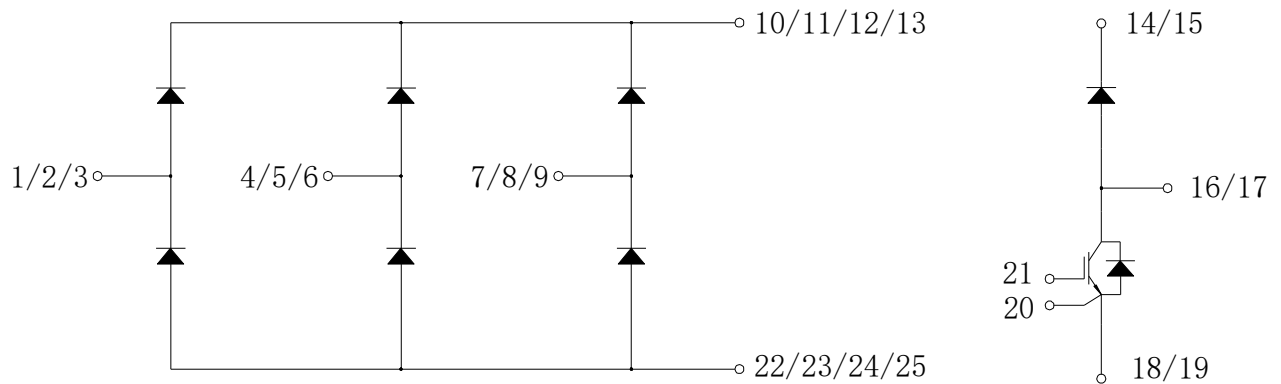


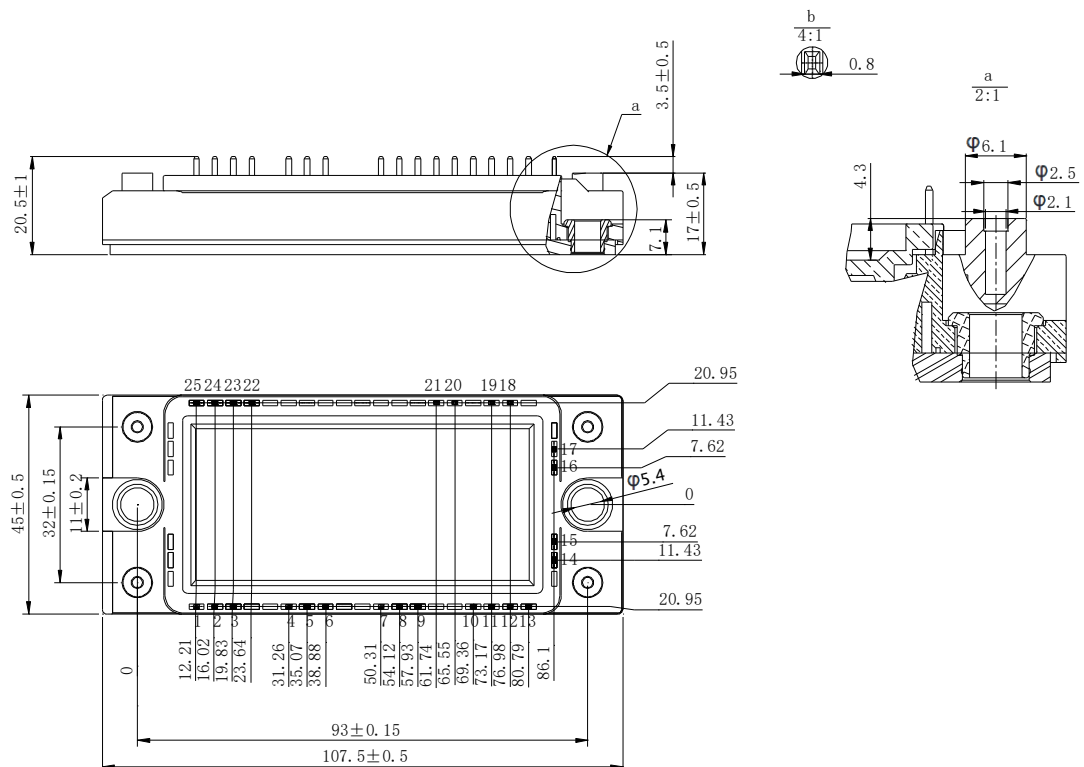
Fig4.Diode -Chopper-Reverse
Foward Characteristics



● Circuit Diagram



● Package Outline Information





Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The data provided in this specification comes from professional testing equipment of Yangjie Electronic Laboratory, not general testing equipment. All the data is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.21yangjie.com](http://www.21yangjie.com) , or consult your nearest Yangjie's sales office for further assistance.